

Ref. No.: Ex/Met/ET/T/222/2019

B.MET.ENGG.2<sup>ND</sup> YR. 2<sup>ND</sup> SEM. EXAM.-2019

APPLIED ELECTRONICS & INSTRUMENTATION

TIME : 3HOURS

FULL MARKS :100

(50 marks for each Part)

Use Separate Answer Scripts for Each Group

GROUP A

FULL MARKS : 50

Answer question no. 1 and any two from the rest (Q.2-Q.4)

1)

- a) What are the different techniques current flows through a semiconductor?
- b) When is a p-n junction diode said to be in (i) forward bias and (ii) reverse bias.
- c) What is the importance of CMRR?
- d) What are the ideal characteristics of an OP-AMP
- e) What do you mean by CMRR & Slew Rate?

5x2=10

2)

- a) Name two elemental and two compound semiconductors.
- b) Define Fermi energy level at T=0K?
- c) Why the effective mass of electron within a crystal is different from free electron mass?
- d) Briefly explain two current conduction mechanisms in a semiconductor.
- e) Find the conductivity of a bar of pure silicon at 300K. Given,  $\mu_n = 0.13\text{m}^2/(\text{V.s})$ ,  $\mu_p = 0.05\text{m}^2/(\text{V.s})$ ,  $n_i = 1.5 \times 10^{16}/\text{m}^3$  and electronic charge  $e = 1.6 \times 10^{-19}$  coulombs .
- f) Define mobility?

(2+3+3+5+5+2)=20

3)

- a) Draw and level the energy band diagram of a p-n junction diode under- equilibrium, forward biased, and reverse biased conditions.
- b) Consider a uniformly doped silicon pn junction with doping concentration  $N_A = 3 \times 10^{17}\text{cm}^{-3}$  and  $N_D = 10^{16}\text{cm}^{-3}$  . What is the value of  $V_{bi}$  (built in potential barrier) at  $T = 300\text{K}$ .  $n_i = 1.5 \times 10^{10}\text{cm}^{-3}$ . Thermal voltage is 26 mV.
- c) Write down the current-voltage equation of p-n junction diode explaining all the symbols used.
- d) The reverse saturation current at 300k of a p-n junction Ge diode is  $5\mu\text{A}$ . Find the voltage to be applied across the junction to obtain a forward current of 50 mA.
- e) What is zener break down ?

6+3+5+3+3 = 20

[ Turn over

- 4)
- What are the different modes of operation of a transistor? Define static characteristics of a transistor?
  - Draw and explain the input and output characteristics of a common emitter mode bipolar junction transistor indicating all regions of operation on the characteristic curve. What is Early effect? Show Early voltage on the characteristic curve.
  - Draw and explain the operation of a centre-tapped full wave rectifier. Find the values for (i) DC load current and (ii) ripple factor of the full wave rectifier.
  - Define transistor biasing. What are the factors determining the choice of the Q- point?
  - Define the three stability factors. Derive the relationship between  $\alpha$  and  $\beta$ .

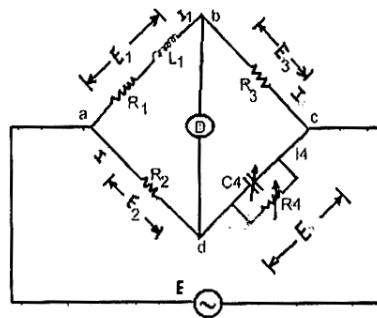
$$((6+2)+(5+2+2)+3)=20$$

### GROUP B

FULL MARKS : 50

Answer question no. 5 and any two from the rest (Q.6-Q.9)

- 5.
- What are the typical detectors used in AC Bridge?
  - What are the advantages of potentiometer type transducer?
  - What are the fundamental transducer parameters?
  - Define gage factor.
  - Briefly explain two element rosettes?
- 5x2 =10
- 6
- In the following bridge  $R_2 = 400$  Ohm,  $R_3 = 600$  Ohm,  $R_4 = 1000$  Ohm,  $C_4 = 0.5$  MicroFarad. Calculate the value of  $R_1$  and  $L_1$ . Calculate the Q of coil if the frequency is 1000Hz.



- Why Kelvin Double Bridge has been used as a modification of Wheatstone Bridge?
- Explain the operation of Kelvin Double Bridge.

$$6+6+8=20$$

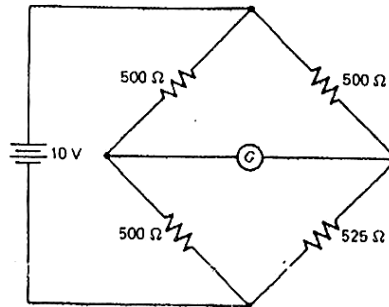
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- The impedance of the basic AC bridge are as follows  $Z_1 = 100 \angle 80^\circ$  Ohm,  $Z_2 = 250$  Ohm,  $Z_3 = 400 \angle 30^\circ$  Ohm and  $Z_4 =$  unknown. Determine the constant for unknown arm.

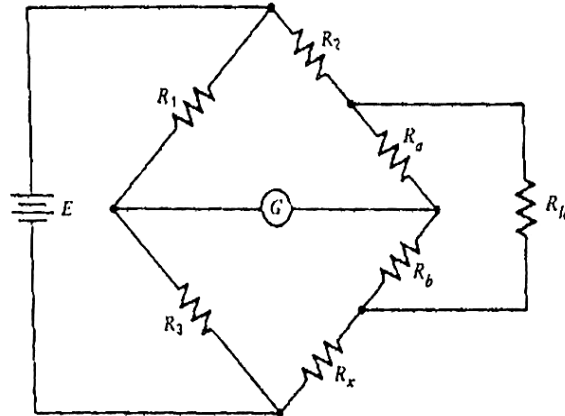
- ii) Explain the operation of Modified De- Sauty's Bridge with proper Phasor diagram. Why it is called as modified.
- iii) Explain the operation of Wien's Bridge. 6+8+6=20

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- i) Calculate the current through the galvanometer from the following figure. Galvanometer resistance is 125 Ohm and it is a center zero 200-0-200 micro-Amp movement



- ii) Explain the operation of Murray loop. How it is different from Varley loop?
- iii) Calculate the  $R_x$  in the following circuit if  $R_a = 1200$  Ohm,  $R_1 = 1.25 R_2$ ,  $R_1 = 800$  Ohm,  $R_b$  and  $R_b = 1600$  Ohm.



5+5+5+5=20

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- i) Proof that the Gage factor depends on Poisson's ratio.
- ii) Briefly describe some metallic sensing element to calculate the strain.
- iii) Explain the operation of LVDT with proper figure.
- iv) A resistance strain gage with a gage factor of 2.4 is mounted on a steel beam whose modulus of elasticity is  $2 \times 10^6$  Kg/cm<sup>2</sup>. The strain gage has an unstrained resistance of 120 Ohm which increases to 120.1 ohm when the beam is subjected to a stress. Calculate the stress at the point where the strain gage is mounted.

5+5+6+4=20